

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFR120N, IIRFR120N

FEATURES Static drain-source on-resistance: Ros(on)≤210mΩ · Enhancement mode: 100% avalanche tested Minimum Lot-to-Lot variations for robust device performance and reliable operation pin 1, Gate 2, Drain DPAK 3, Source DESCRITION TO-252 Package · Fast switching C 0.5 ABSOLUTE MAXIMUM RATINGS(Ta=25°C) K SYMBOL VALUE UNIT PARAMETER C VDSS Drain-Source Voltage 100 V D V_{GS} Gate-Source Voltage ± 20 V Drain Current-Continuous 9.4 ΙD А 3.0 Drain Current-Single Pulsed 38 А **I**DM F \mathbf{P}_{D} Total Dissipation @Tc=25°C W 48 G H H Max. Operating Junction Temperature °C Τį 175 mm Storage Temperature -55~175 °C Tstg MAX DIM MIN 6.40 6.60 А 5.20 5.40 В THERMAL CHARACTERISTICS 1.15 35 D 5. 70 6. 10 SYMBOL PARAMETER MAX UNIT н 10 50 Channel-to-case thermal resistance °C/W Rth(j-c) 3.1 2 10 40 K 0.40 0. 60 0.90 Channel-to-ambient thermal resistance °C/W Rth(j-a) 110 9.90 0

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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	100			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =250 µ A	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =5.6A			210	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			25	μA
V _{SD}	Diode forward voltage	I _s =5.5A, V _{GS} = 0V			1.3	V

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